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Sommario/riassunto

Crystal growth technology involves processes for the production of crystals essential for microelectronics, communication technologies, lasers and energy producing and energy saving technology. A deliberately added impurity is called an additive and in different industries these affect the process of crystal growth. Thus, understanding of interactions between additives and the crystallizing phases is important in different processes found in the lab, nature and in various industries. This book presents a generalized description of the mechanisms of action of additives during nucleation, grow